UP1496

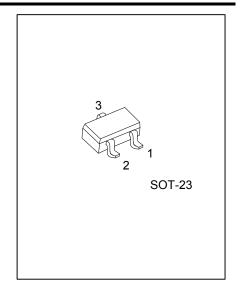
Preliminary

PNP SILICON TRANSISTOR

PNP SILICON PLANAR HIGH VOLTAGE TRANSISTOR

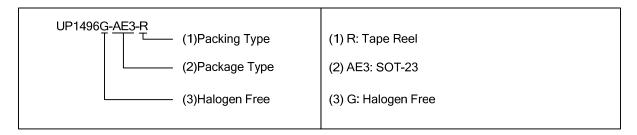
■ DESCRIPTION

The UTC **UP1496** are series of PNP silicon planar transistors which have gain of 500 at $I_{\rm C}$ =100mA. It can be used in such applications like battery powered circuits and darlington replacements.



ORDERING INFORMATION

Ordering Number	Package	Pin Assignment			Dooking	
		1	2	3	Packing	
UP1496G-AE3-R	SOT-23	Е	В	С	Tape Reel	



■ MARKING



■ ABSOLUTE MAXIMUM RATINGS

PARAMETER	SYMBOL	RATINGS	UNIT
Collector-Base Voltage	V_{CBO}	-220	٧
Collector-Emitter Voltage	V_{CEO}	-200	٧
Emitter-Base Voltage	V_{EBO}	-5	٧
Collector Current	Ic	-0.3	Α
Peak Pulse Current	I _{CM}	-1	Α
Base Current	I _B	-200	mA
Collector Dissipation (T _a =25°C)	Pc	500	mW
Junction Temperature	TJ	+150	°C
Storage Temperature	T _{STG}	-55 ~ + 150	Ô

Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

■ ELECTRICAL CHARACTERISTICS (T_a=25°C, unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS		TYP	MAX	UNIT
Collector-Base Breakdown Voltage	BV_CBO	I _C =-100 μA	-220			V
Collector-Emitter Breakdown Voltage	BV_CEO	I _C =-10 mA (Note)	-200			V
Emitter-Base Breakdown Voltage	BV_{EBO}	I _E =-100 μA	-5			V
Collector Cutoff Current	I _{CBO}	V _{CB} =-200 V			-100	nA
Emitter Cutoff Current	I _{EBO}	V _{EB} =-4 V			-100	nA
Collector -Emitter Cut-off Current	I _{CES}	V _{CES} =-200 V			-100	nA
DC Current Transfer Ratio	h _{FE}	V_{CE} =-10V , I_{C} =-1mA	100			
		V _{CE} =-10V , I _C =-100mA (Note)	100			
		V _{CE} =-10V , I _C =-250mA (Note)	85		300	
		V _{CE} =-10V , I _C =-400mA (Note)	35			
Base-Emitter Turn-On Voltage	$V_{BE(ON)}$	V _{CE} =-10V , I _C =-250 mA (Note)			-0.9	V
Collector-Emitter Saturation Voltage	VCE(SAT)	I _C =-100mA, I _B =-10mA			-0.2	V
		I _C =-250mA, I _B =-25mA (Note)			-0.35	V
Base-Emitter Saturation Voltage	$V_{BE(SAT)}$	I _C =-250mA, I _B =-25mA (Note)			-1.0	V
Transition Frequency	f_T	V_{CE} =-10V , I_{C} =-50mA, f=100MHz	150			MHz
Output Capacitance	Сов	V _{CB} =-10V, f=1MHz			10	pF

Note: Measured under pulse conditions. Pulse width=300µs. Duty cycle≤2%.

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